SPE RESPONSE FOR CERTIFICATE OF CORRECTION

		Pape	r No.:20060927		
DATE : Septemb	er 27, 2006				
TO SPE OF : ART UN	T 2813		;		
SUBJECT : Request	UBJECT: Request for Certificate of Correction on Patent No.: 7,022,555				
A response is requested v	vith respect to the accom	npanying request for a certificate of c	correction.		
Please complete this for Certificates of Correct Palm location 7590 - Te	ion Branch - PK 3-91	•			
With respect to the change(s) requested, correcting Office and/or Applicant's errors, should the patent read as shown in the certificate of correction? No new matter should be introduced, nor should the scope or meaning of the claims be changed.					
Thank You For Your A	ssistance	Certificates of Correction	Branch		
The request for issuing the above-identified correction(s) is hereby: Note your decision on the appropriate box.					
⊠ Approved		All changes apply.			
☐ Approved in	Part	Specify below which changes do r	not apply.		
☐ Denied		State the reasons for denial below			
Comments:					
		SPE: Carl Whitehead, Jr.	Art Unit 2813		

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page 1 of 2

PATENT NO.

7,022,555

APPLICATION NO.

10/774,515

ISSUE DATE

April 4, 2006

INVENTORS

John T. Moore et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patents portion of the References Cited section, add the following two patents:

4,673,957

6/1987

Ovshinsky et al.

5,335,219

8/1994

Ovshinsky et al.

In the Other Publications portion of the References Cited section, add the following applications:

U.S. Appl. No. 09/779,983, filed Feb. 2001, Moore.

U.S. Appl. No. 09/943,190, filed Aug. 2001, Campbell, et al.

U.S. Appl. No. 09/943,199, filed Aug. 2001, Campbell, et al.

U.S. Appl. No. 09/943,187, filed Aug. 2001, Campbell, et al.

U.S. Appl. No. 10/077,867, filed Feb. 2002, Campbell, et al.

U.S. Appl. No. 10/232,757, filed Aug. 2002, Li, et al.

Also in Other Publications, on page 7, delete the following:

U.S. Appl. No. 5,238,862, filed Aug. 1993, Blalock et al.

U.S. Appl. No. 5,360,981, filed Nov. 1994, Owen, et al.

U.S. Appl. No. 5,761,115, filed Jun. 1998, Kozicki, et al.

MAILING ADDRESS OF SENDER (Please do not use customer number below): Thomas J. D'Amico **DICKSTEIN SHAPIRO LLP** 1825 Eye Street, NW Washington, DC 20006-5403

The So and

Approved for use through 04/30/2007. OMB 0651-0033
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

U.S. Appl. No. 5,896,312, filed Apr. 1999, Kozicki et al.

U.S. Appl. No. 5,914,893, filed Jun. 1999, Kozicki et al.

U.S. Appl. No. 6,084,796, filed Jul. 2000, Kozicki et al.

In the Specification, the following error is corrected:

Column 2, line 16, "metal is ion" should read --metal ion --.

In Other Publications, the following typographical errors are corrected:

"Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1992) 14650-14652."

Should read

--Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.--;

"Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Agphotodoped amorphous As₂S₃ films". Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 278-2772."

Should read

--Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Agphotodoped amorphous As₂S₃ films³. Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 2767-2772.--.

In Other Publications, Applicants made the following typographical errors to be corrected:

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Aq-Ge-Se: lonic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. Sep. 9-13, 1985."

Should read

-- Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.: Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: lonic conduction and EXAFS structural investigation, Transportstructure relations in fast ion and mixed conductors, Proc. of the 6th RISO Int'l Symp. Sep. 9-13, 1985.--;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTI chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.—.

MAILING ADDRESS OF SENDER (Please do not use customer number below): Thomas J. D'Amico DICKSTEIN SHAPIRO LLP 1825 Eye Street, NW Washington, DC 20006-5403



Docket No.: M4065.0697/P697-A

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of: John T. Moore et al.

Patent No.: 7,022,555

Issued: April 4, 2006

For: METHODS OF FORMING A

SEMICONDUCTOR MEMORY DEVICE

REQUEST FOR CERTIFICATE OF CORRECTION PURSUANT TO 37 C.F.R. §§1.322 & 1.323

Attention: Certificate of Correction Branch Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted typographical and other errors which should be corrected.

In the U.S. Patents portion of the References Cited section, the PTO omitted the following two patents from the IDS dated July 15, 2004 (attached as ExhibitA, Page 1), which should be added:

4,673,957	6/1987	Ovshinsky ef 47.5/2006 TRESHAH1 1990	9989 7922555
, ,	·	01 FC:1811	188.89 OP
5,335,219	8/1994	Ovshinsky et al.	